Prisemi®

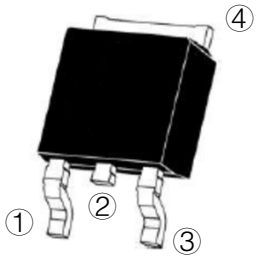
PNMDP30V90A

N-Channel MOSFET

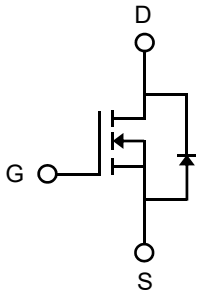
Description

The PNMDP30V90A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a load switch or in PWM applications.

MOSFET Product Summary		
V_{DS}(V)	$R_{DS(on)}$(mΩ)	I_D(A)
30	4.0@ V_{GS} = 10V	70
	5.5@ V_{GS} = 4.5V	



TO-252 (Top View)



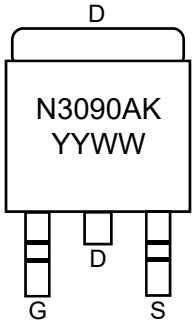
Circuit Diagram

Feature

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Applications

- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



Marking (Top View)

Absolute maximum rating@25℃

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous[1)]	T_C=25℃	I_D	70	A
	T_C=100℃		44.6	
Pulsed Drain Current[2)]		I_{DM}	280	A
Total Power Dissipation[3)]		P_D	39.8	W
Avalanche Current[4)]		I_{AS}	49.2	A
Avalanche Energy[4)]		E_{AS}	121	mJ
Thermal Resistance , Junction-case[5)]		$R_{\theta JC}$	7.0	℃/W
Thermal Resistance Junction-to-Ambient[5)]		$R_{\theta JA}$	42.5	℃/W
Junction and Storage Temperature Range		T_J,T_{STG}	-55~+150	℃

Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V,I_D = 250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V,V_{GS} = 0V	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V,V_{DS} = 0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS},I_D = 250μA	1.0	1.6	2.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} = 10V,I_D = 25A	-	4.0	5.5	mΩ
		V_{GS} = 4.5V,I_D = 20A	-	5.5	8.0	
Dynamic Characteristics[6)]						
Input Capacitance	C_{lss}	V_{DS} = 15V,V_{GS} = 0V, f = 1.0MHz	-	2551	-	pF
Output Capacitance	C_{oss}		-	329	-	
Reverse Transfer Capacitance	C_{rss}		-	266	-	
Switching Characteristics[6)]						
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 15V, V_{GS} = 10V, R_G = 10Ω, I_D = 20A	-	8.9	-	ns
Turn-on Rise Time	t_r		-	21.4	-	
Turn-Off Delay Time	$t_{d(off)}$		-	79	-	
Turn-Off Fall Time	t_f		-	37	-	
Total Gate Charge	Q_g	V_{DS} = 15V, V_{GS} = 10V, I_D = 20A	-	48.4	-	nC
Gate-Source Charge	Q_{gs}		-	6.7	-	
Gate-Drain Charge	Q_{gd}		-	8.2	-	
Gate Resistance	R_g	V_{GS}=0V,V_{DS}=0V,f=1MHz	-	2.0	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V,I_S = 20A	-	0.85	1.3	V

Notes:
1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature(T_{J_Max}=150℃).
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. This single-pulse measurement was taken under the following condition (L=100uH,V_{GS}=10V,V_{DS}=50V)while it's value is limited by T_{J_Max}=150℃.
5. Device mounted on infinite heatsink.
6. Guaranteed by design, not subject to production.

Typical Characteristics

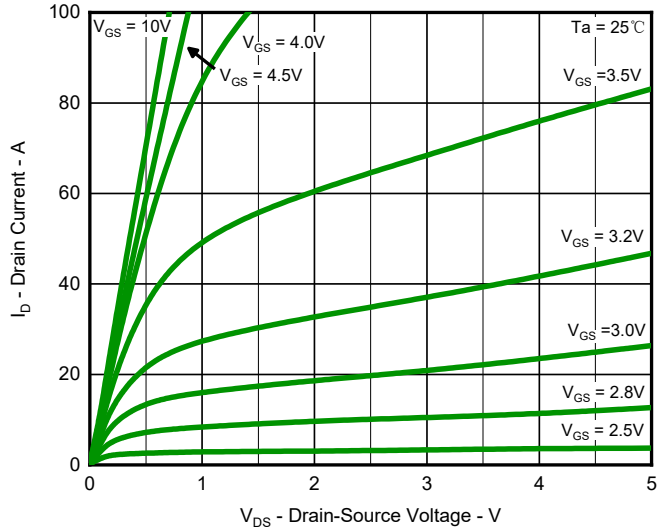


Fig.1 Output Characteristics

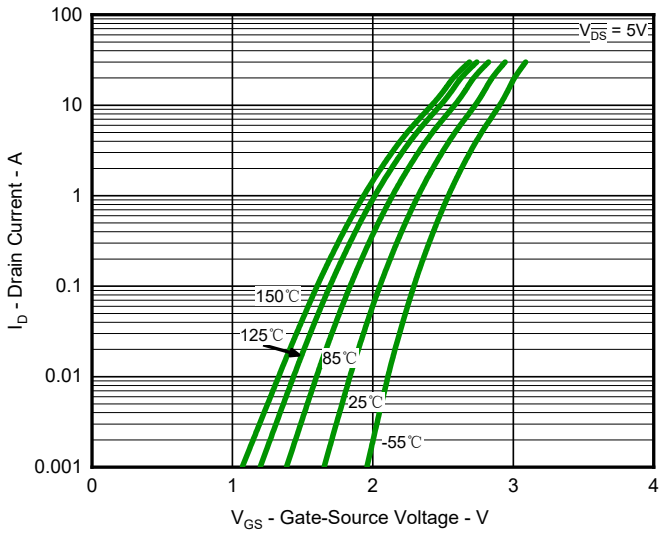


Fig.2 Typical Transfer Characteristic

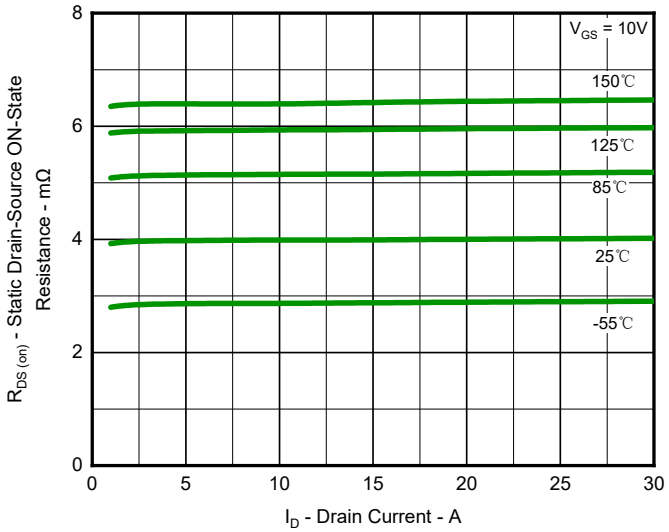


Fig.3 Typical On-Resistance vs Drain Current and Temperature

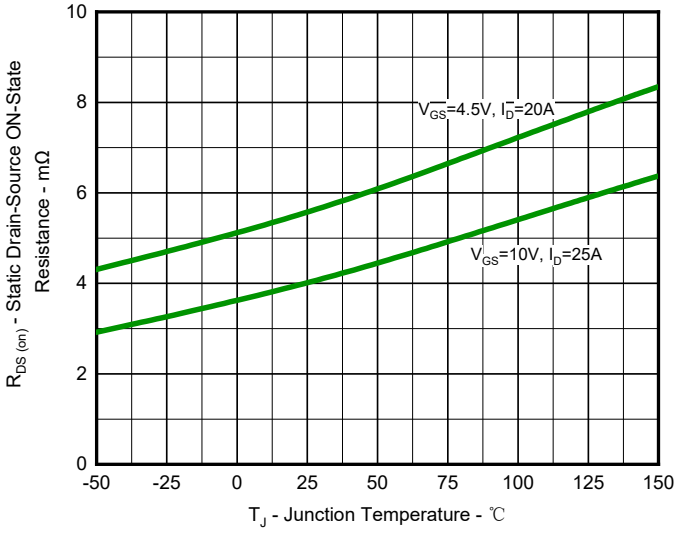


Fig.4 On-Resistance Variation with Temperature

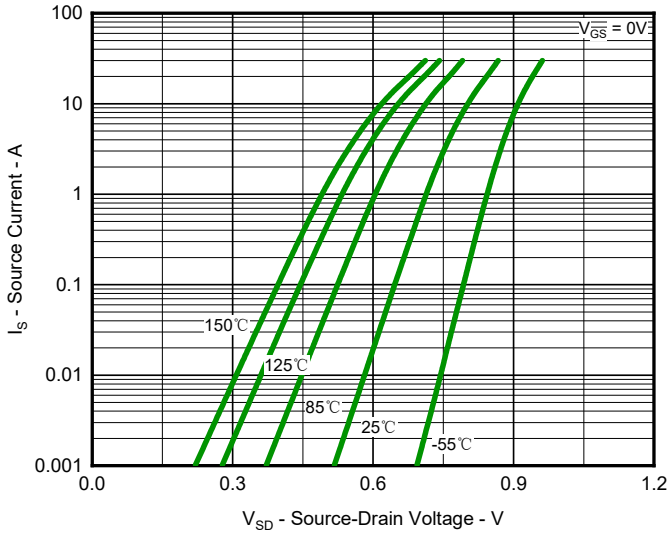


Fig.5 Diode Forward Voltage vs. Current

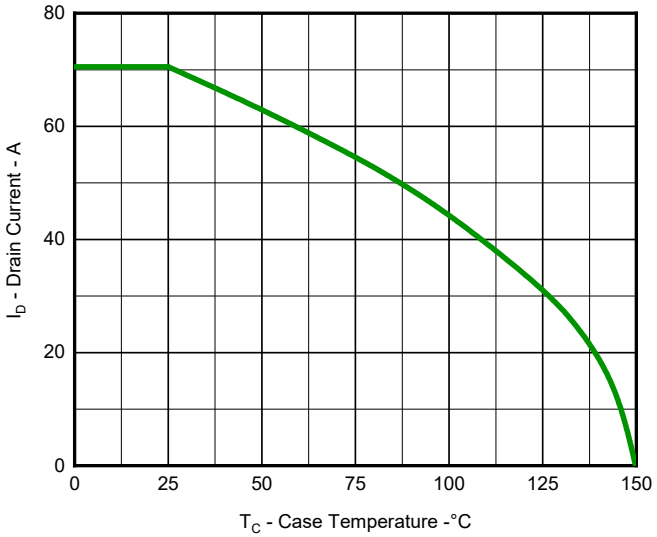


Fig.6 Maximun Drain Current vs. Case Temperature

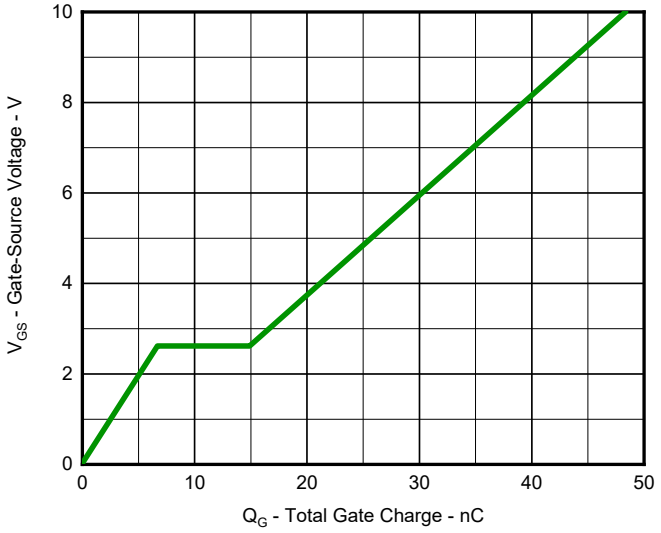


Fig.7 Gate Charge Characteristics

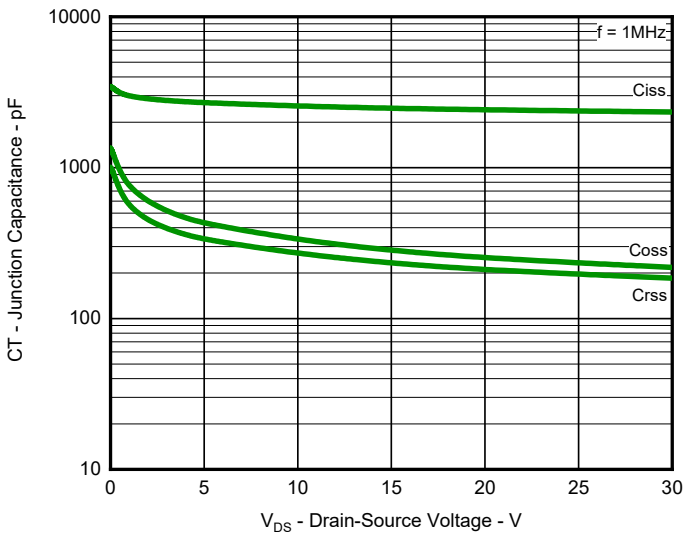


Fig.8 Typical Junction Capacitance

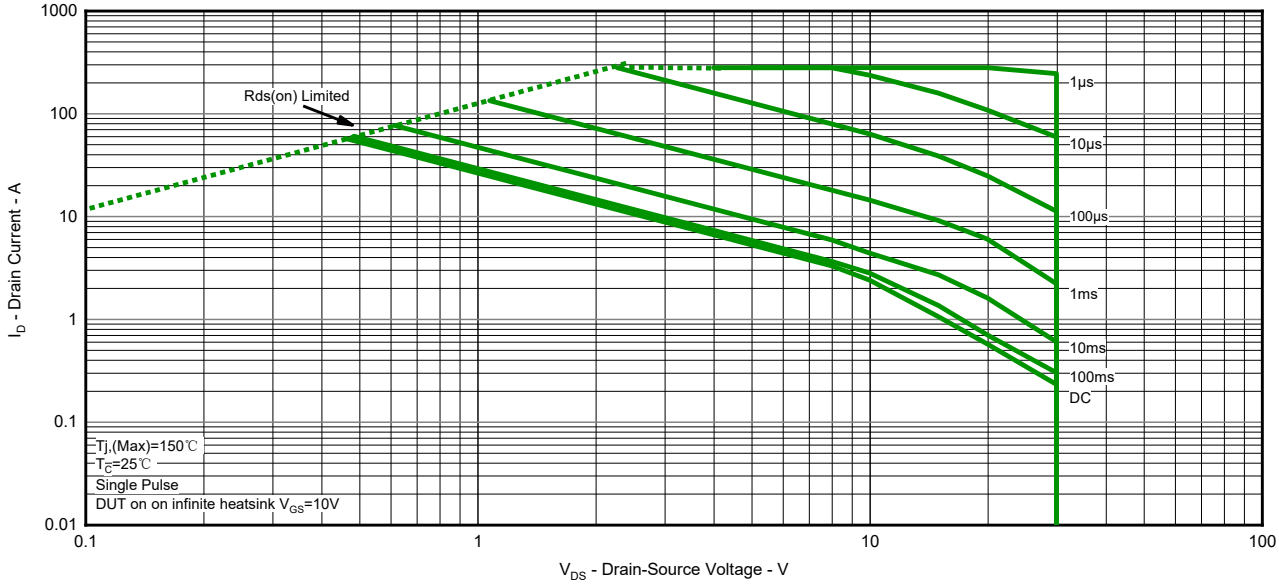


Fig.9 Safe Operation Area

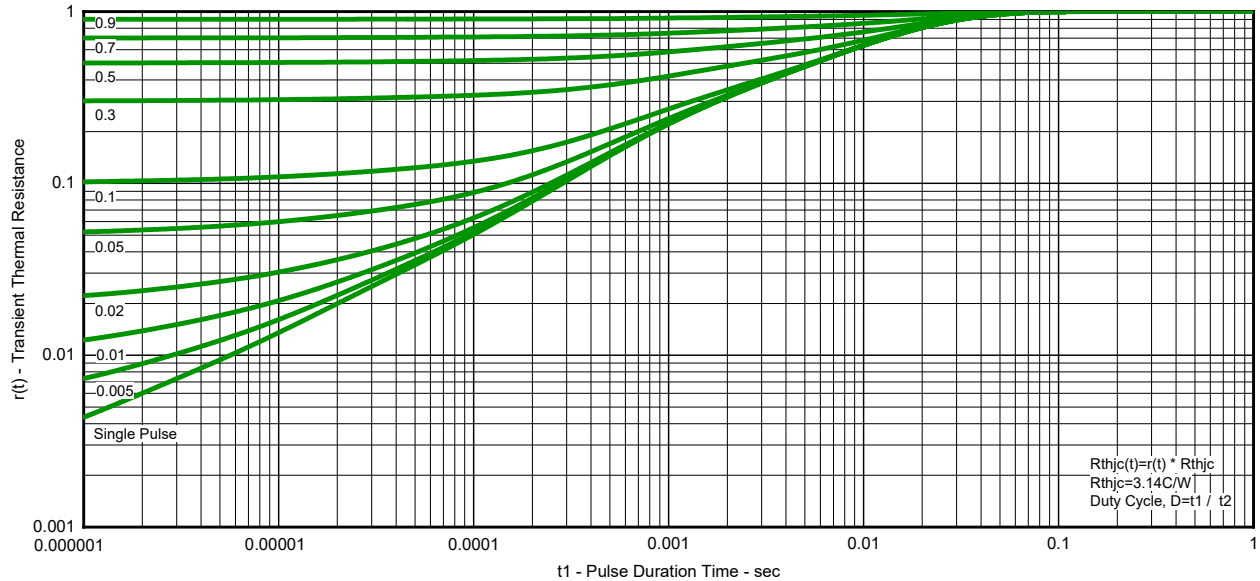
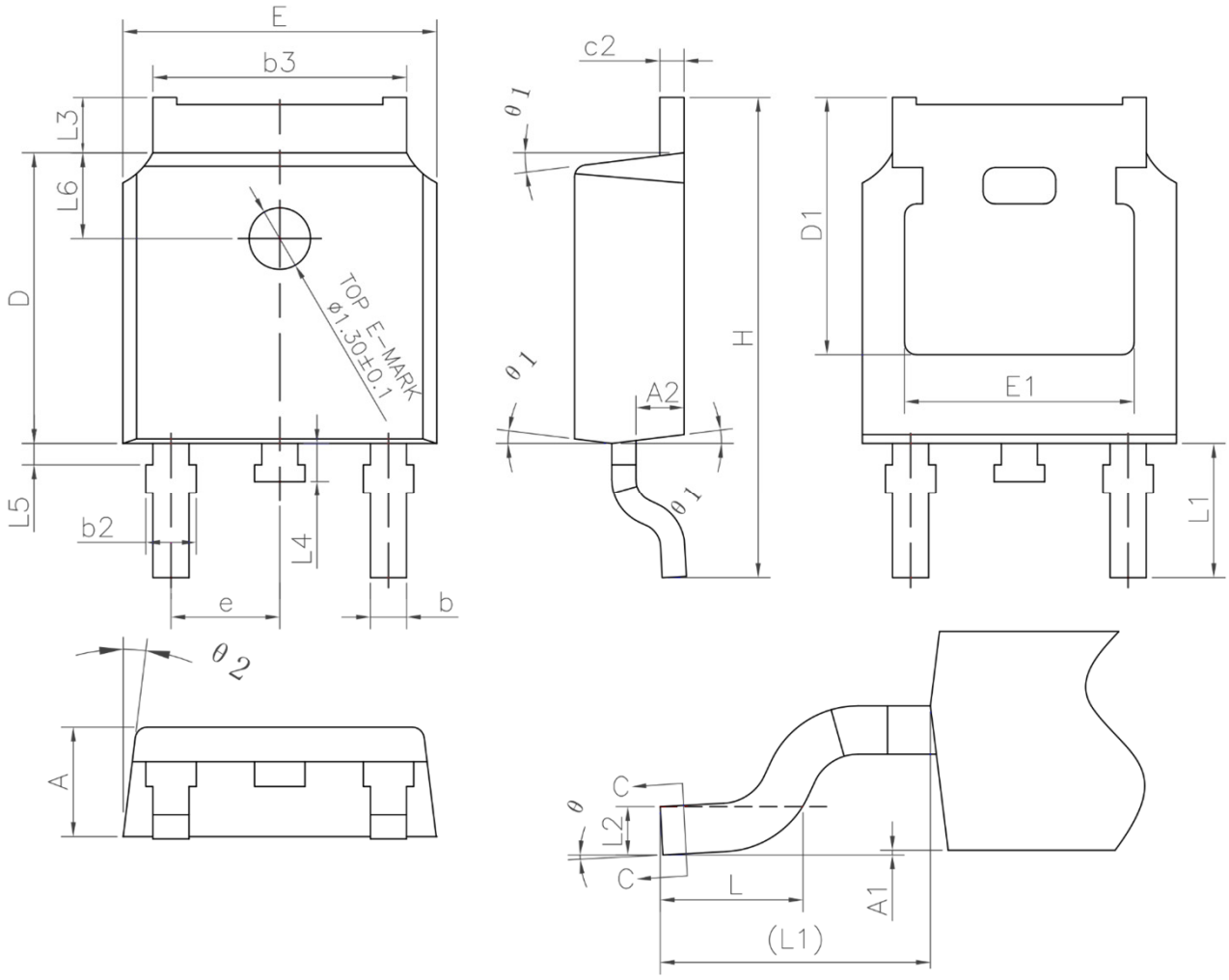


Fig.10 Transient Thermal Resistance

Product Dimension (TO-252)

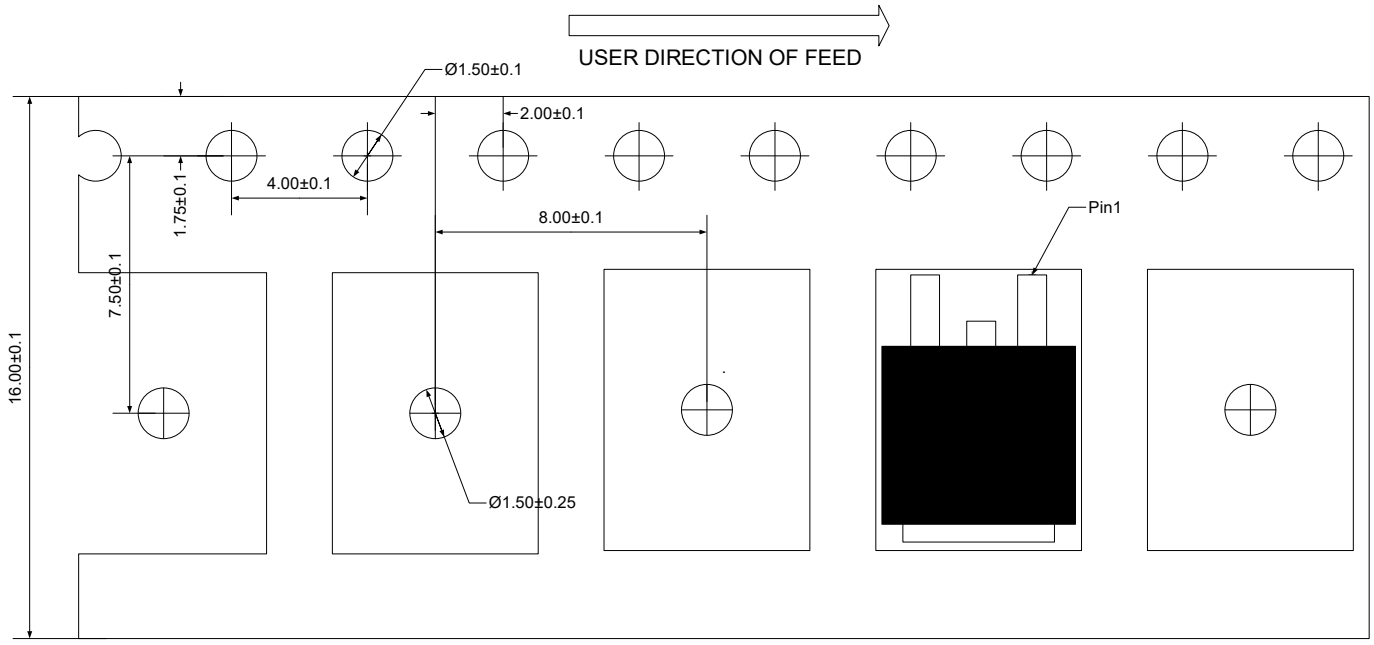


Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	2.20	2.38	0.087	0.094	e	2.186	2.386	0.086	0.094
A1	0.00	0.10	0.000	0.004	H	9.80	10.40	0.386	0.409
A2	0.90	1.10	0.035	0.043	L	1.40	1.70	0.055	0.067
b	0.72	0.82	0.028	0.032	L1	2.90 Ref.		0.114 Ref.	
b2	0.72	0.90	0.028	0.035	L2	0.508 BSC.		0.020 BSC.	
b3	5.13	5.46	0.202	0.215	L3	0.90	1.25	0.035	0.049
c	0.47	0.60	0.019	0.024	L4	0.60	1.00	0.024	0.039
c2	0.47	0.60	0.019	0.024	L5	0.15	0.75	0.006	0.030
D	6.00	6.20	0.236	0.244	L6	1.80 Ref.		0.071 Ref.	
D1	5.25	-	0.207	-	θ	0°	8°	0°	8°
E	6.50	6.70	0.256	0.264	θ1	5°	9°	5°	9°
E1	4.70	-	0.185	-	θ2	5°	9°	5°	9°

Ordering Information

Device	Package	Reel	Shipping
PNMDP30V90A	To-252	13"	2500 / Tape & Reel

Load With Information



Unit:mm

IMPORTANT NOTICE

Prisemi® and Prisemi® are registered trademarks of **Prisemi Electronics Co., Ltd** (Prisemi**),** Prisemi reserves the right to make changes without further notice to any products herein. Prisemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Prisemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. “Typical” parameters which may be provided in Prisemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including “Typicals” must be validated for each customer application by customer’s technical experts. Prisemi does not convey any license under its patent rights nor the rights of others. The products listed in this document are designed to be used with ordinary electronic equipment or devices, Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

Website: http://www.prisemi.com
For additional information, please contact your local Sales Representative.